AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (original) An improved p-type gallium nitride-based semiconductor device comprising:

a device structure that includes at least one p-type Group III nitride layer that includes some gallium;

a first silicon dioxide layer on said p-type layer;

a layer of a Group II metal source composition on said first SiO_2layer; and

a second SiO_2 layer on said Group II metal source composition layer.

2. (original) A semiconductor device according to Claim 1 wherein said device structure comprises:

a conductive silicon carbide substrate;

a conductive buffer layer on said silicon carbide substrate for providing a crystal transition between said substrate and said Group III nitride portions of said device; and

an n-type Group III nitride layer on said buffer layer.

3. (original) A device according to Claim 1 wherein said first silicon dioxide layer is thick enough to create vacancies to a depth in said p-type layer that encourages atoms of said Group II metal to diffuse thereinto while still permitting diffusion from said Group II metal source composition through said first SiO_2 layer and into said p-type layer.

4. (original) A device according to Claim 1 wherein:

said first SiO_2 layer is about 1000 Å thick;

said Group II metal source composition layer is about 1000 Å thick; and

said second SiO_2 layer is about 2500 Å thick.

5. (original) A device according to Claim 1 wherein said Group III nitride comprises GaN and said source composition layer is selected from the group consisting of magnesium and zinc.

6. (cancelled)

7. (previously amended)A device structure according to Claim 2 wherein said substrate is n-type and has a carrier concentration of between about 1 X 10^{16} cm^{-3} and about 1 X 10^{19} cm^{-3} .

8. (original) A device according to Claim 1 wherein said Group II metal source composition layer comprises a Group II metal-containing compound.

9. (original) A device according to Claim 8 wherein said compound is selected from the group consisting of magnesium nitride and zinc phosphide.

10. (previously amended) A device according to Claim 1 wherein said p-type gallium nitride layer has the formula $Ga_xAl_yIn_{1-x-y}N$ where $0 < x \leq 1$ and $0 \leq y \leq 1$.

11. (original) A device according to Claim 1 comprising a plurality of silicon dioxide portions on said p-type Group III nitride layer, with a respective portion of said source composition on each said silicon dioxide portion.

12. (currently amended) ~~A device according to Claim 11~~ An improved p-type gallium nitride-based semiconductor device comprising:

a device structure that includes at least one p-type Group III nitride layer that includes some gallium;

a plurality of silicon dioxide portions on said p-type Group III nitride layer;

a portion of a Group II metal source composition layer on each of said silicon dioxide portions; and

a second silicon dioxide layer on said Group II metal source composition layer,

wherein said second silicon dioxide layer is limited to said source composition layer portions.

13. (original) A device according to Claim 11 wherein said second silicon dioxide portion covers said source composition portions and portions of said p-type Group III nitride layer.

14. (original) An improved p-type gallium nitride-based device comprising:

a conductive silicon carbide substrate;

a conductive buffer layer on said silicon carbide substrate for providing a crystal transition between said substrate and said GaN portions of said device;

an n-type GaN layer on said buffer layer;

a p-type GaN layer on said n-type layer;

a first silicon dioxide layer on said p-type layer;

a magnesium layer on said first SiO_2 layer for supplying p-type dopant to said p-type layer; and

a second SiO_2layer on said Mg layer for passivating said device;

said first silicon dioxide layer being thick enough to create vacancies to a required depth in said p-GaN layer when said device is heated to temperatures between about 750° and 950° C while still permitting diffusion from the magnesium layer through said first SiO_2 layer and into the p-GaN layer at such temperatures.

15. (original) A device according to Claim 14 wherein said substrate is n-type.

16. (original) A device according to Claim 14 wherein said buffer is selected from the group consisting of: graded layers of Group III nitrides, homogeneous layers of Group III nitrides, heterogeneous layers of Group III nitrides and combinations thereof.

17. (original) A device according to Claim 14 wherein said n-type layer comprises $Al_xIn_yGa_{1-x-y}N$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$

18. (currently amended) A device according to Claim 14 wherein said p-type layer comprises ~~$Ga_xAl_yIn_{1-x-y}$~~ $Ga_xAl_yIn_{1-x-y}N$ where $0 < x \leq 1$ and $0 \leq y \leq 1$.

19-44. (cancelled)